

SKM100GB101D Transistors

Half Bridge IGBT Power Module

Isolated Case (Y/N) Yes

Circuits Per Package 1

V(BR)CES (V) 1.0k

V(BR)GES (V) 20

I(C) Max. (A) 100

Absolute Max. Power Diss. (W) 625

Minimum Operating Temp (°C)

Maximum Operating Temp (°C) 150

Thermal Resistance Junc-Case .2

I(CES) Min. (A) 1.4m

@V(CES) (V) (Test Condition)

I(GES) Max. (A) 100n

@V(GES) (V) (Test Condition)

V(CE)sat Max. (V) 4.0

@I(C) (A) (Test Condition)

@V(GE) (Test Condition)

V(GE)th Max. (V)

@I(C) (A) (Test Condition)

@V(CE) (V) (Test Condition)

g(fe) Min. (S) Trans. admitt.

q(fe) Max. (S) Trans. admitt.